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*only abstract.*

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TITLE: MANUFACTURE OF MOS TYPE SEMICONDUCTOR DEVICE

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*used for claims 1, 11, 12, 13*

INVENTOR-INFORMATION:

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ABSTRACT:

PURPOSE: To reduce the cost by a method wherein lead-out electrodes from the source and drain of an MOS type TFT formed on a glass substrate are created by the printing method.

CONSTITUTION: A semiconductor film 2 is formed on the surface of the glass substrate 1. First, resist is formed into a figure form by printing, and next the resist is removed by etching with the mixed solution of HF and HNO<sub>3</sub>. Then, an Si<sub>3</sub>N<sub>4</sub> film 3 is formed by the plasma CVD method. Through holes for leading out the source and drain electrodes are formed in the film 3. The source, gate, and drain electrodes 4, 5, and 6 are formed by printing an ink of the mixture of W or Mo powder in a binder such as glycerin by the printing method such as screen printing, and then by solidification.

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